

INFORMATION DISCLOSURE CITATION <i>(Use several sheets if necessary)</i>				ATTY DOCKET NO. YO999-153D		SERIAL NO. Not Yet Assigned	
				APPLICANT(S) Chen, et al.			
				FILING DATE Concurrently Herewith		GROUP Not Yet Assigned	
U.S. PATENT DOCUMENTS							
*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE	
ON	5,493,137	02/20/96	Satoh et al.				
ON	5,585,284	12/17/96	Park				
ON	5,258,318	11/02/03	Buti et al.				
ON	5,508,219	04/16/96	Bronner et al.				
ON	6,015,745	01/18/00	Adkisson et al.				
ON	5,956,597	09/21/99	Furukawa et al.				
ON	5,930,638	07/27/99	Reedy et al.				
ON	5,891,763	04/06/99	Wanlass				
ON	5,830,784	11/03/98	Zhang et al.				
ON	5,399,507	03/21/95	Sun				
ON	5,373,803	12/20/94	Noguchi et al.				
FOREIGN PATENT DOCUMENTS							
	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)							
ON			Neudeck, G., "A New Epitaxial Lateral Overgrowth Silicon Bipolar Transistor", IEEE Electron Device Letters, Vol. EDL-8, No. 10, October 1987, pp. 492-495.				
ON			Zingg, et al., "Three-Dimensional Stacked MOS Transistors by Localized Silicon Epitaxial Overgrowth", IEEE Transactions on Electron Devices, Vol. 37, No. 6, June 1990, pp. 1452-1461.				
EXAMINER <div style="text-align: center; font-size: 1.5em;">ON</div>				DATE CONSIDERED <div style="text-align: center; font-size: 1.5em;">3/23/01</div>			
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